

FORM PTO-1449 (Modified)				ATTY. DOCKET NO. YOR919990123US2		SERIAL NO.: 09/936,320	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				APPLICANT: Jack O. Chu			
(Use several sheets if necessary)				FILING DATE: September 12, 2001		GROUP: 2811	

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PATENT & TRADEMARK OFFICE

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS					
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
h	AA	5,019,882	05/28/1991	Solomon et al.	357	23.8	May 15, 1989
h	AB	5,534,713	07/09/1996	Ismail et al.	257	24	May 20, 1994
h	AC	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
h	AD	5,298,452	03/29/1994	Meyerson	437	81	February 21, 1992
h	AE	5,659,187	08/19/1997	Legoues et al.	257	190	June 7, 1995
h	AF	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
h	AG	5,259,918	11/09/1993	Akbar et al.	156	610	June 12, 1991
	AH						


FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
h	AJ	05 121450 A	15/05/1993	Japan	H01L	21/338	

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
h	AM R. People and J.C. Bean, "Band Alignments Of Coherently Strained Ge _x Si _{1-x} / Si Heterostructures On <001> Ge _x Si _{1-x} Substrates"; Appl. Phys. Lett. 48 (8); pp. 538-539; February 24, 1986.
h	AN G. Hock et al., "High Performance 0.25μm p-Type Ge/SiGe MODFETs"; Electronics Letters; Vol. 34; No. 19; pp. 1888-1889; September 17, 1998.
h	AO U. Konig and F. Schaffler, "p-Type Ge-Channel MODFET's With High Transconductance Grown On Si Substrates"; IEEE Electron Device Letters; Vol. 14; No. 4; pp. 205-207; April 1993.

EXAMINER	DATE CONSIDERED
	11/05/02




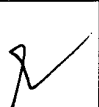
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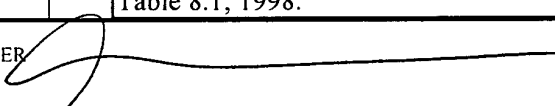
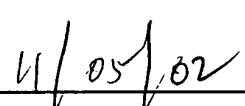
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	BA						
	BB						
	BC						

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	BD						
	BE						
	BF						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
	BE M. Arafa, "A 70-GHz f_T Low Operating Bias Self-Aligned p-Type SiGe MODFET"; IEEE Electron Device Letters; Vol. 17; No. 12; pp. 586-588; December 1996.
	BF U. Kong et al., "SiGe HBTs And HFETs"; IEEE Solid State Electronics; Vol. 38; No. 9; pp. 1595-1602; Elsevier; 1995.
	BG Milind Gokhale et al., "Enhanced Performance Of PMOS and CMOS Circuits Using Self-Aligned MOSFETs With Modulation Doped Si-Ge Channel"; Proceedings of the Tenth Biennial University/ Government/Industry Microelectronics Symposium; 1993 IEEE; US; New York; pp.219-222; May 18-19, 1993.
	BH David W. Greve, "Field Effect Devices And Applications"; Prentice-Hall, Inc; Simon & Schuster/ A Viacom Company; Upper Saddle River, NJ, 07458; Chap. 8: Structure Of The GaAs MESFET; p.315; Table 8.1; 1998.

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